

BD135

1.5 A, 45V NPN Power Bipolar Junction Transistor

Product Overview

For complete documentation, see the data sheet.

This series of plastic, NPN Power Bipolar Junction Transistor transistors are designed for use as audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

Features

- Minimum Gain hFE = 40 @ IC = 150 mA
- BD135, BD137, BD139 are complementary with BD136, BD138, BD140
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

Power supplies

Benefits

Low base drive

End Products

Power supplies

Part Electrical Specifications																	
Product	Pricing (\$/Unit)	Complian ce	Stat	Pola rity	Тур	V _{CE(s} at) Max (V)	I _C Con t. (A)	V _{CEO} Min (V)	V _{CBO} (V)	V _{EBO} (V)	V _{BE(s}	V _{BE(on)} (V)	h _{FE} Min	h _{FE} Max	f _T Min (MH z)	P _{TM} Max (W)	Pac kag e Typ e
BD135G	0.2276	Pb H	Acti ve	NPN	Gen eral Pur pos e	0.5	1.5	45					40	250	-	12.5	TO- 225 -3
BD135TG	0.2407	Pb H	Acti ve	NPN	Gen eral Pur pos e	0.5	1.5	45					40	250	-	12.5	TO- 225 -3